## LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

- 1. (Previously Presented) A DC-DC converter comprising:
- a synchronous semiconductor device; and
- a control semiconductor device;
- wherein at least one of said semiconductor devices includes:
- a semiconductor body of a first conductivity which includes a channel region of a second conductivity and a major surface;

an active region formed in said semiconductor body, said active region including a trench less than 0.5 microns wide extending through said channel region and a gate structure disposed in said trench which includes a gate oxide layer disposed at least on said sidewalls of said trench and a gate electrode disposed adjacent said gate oxide layer; and

- a termination structure, said termination structure including,
- a termination trench formed in said semiconductor body, and a field oxide layer formed in said termination trench below said major surface, wherein said field oxide layer is thicker than said gate oxide layer.
  - 2. Canceled.
  - Canceled.
- 4. (Previously Presented) A semiconductor device according to claim 1, wherein said trench include an oxide mass formed at its bottom said oxide mass being thicker than said gate oxide layer.
- 5. (Original) A semiconductor device according to claim 4, wherein said semiconductor body includes conductive regions of said first conductivity formed adjacent said trench in said channel region, and further comprising a semiconductor substrate of said conductivity, said semiconductor body being formed over said semiconductor substrate, wherein

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said conductive regions are electrically connectable to said semiconductor substrate through invertible channels adjacent said trench.

- 6. (Original) A semiconductor device according to claim 5, wherein said conductive regions are source regions.
- 7. (Previously Presented) A semiconductor device according to claim 1, wherein the depth of said trench has been selected to achieve an optimum figure of merit.
- 8. (Previously Presented) A semiconductor device according to claim 1, wherein said trench is a stripe.
- (Previously Presented) A semiconductor device according to claim 1, wherein 9. said trench is a cell.
- 10. (Original) A semiconductor device according to claim 9, wherein said cell is hexagonal.